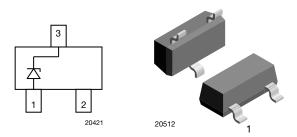
Single-Line ESD Protection in SOT-23



www.vishay.com

MARKING (example only)



YYY = type code (see table below) XX = date code

DESIGN SUPPORT TOOLS click logo to get started



FEATURES

- Single-line ESD protection device
- ESD immunity acc. IEC 61000-4-2 ± 30 kV contact discharge ± 30 kV air discharge
- ESD capability according to AEC-Q101: human body model: class H3B: > 8 kV
- Space saving SOT-23 package
- e3 Sn
- AEC-Q101 qualified available
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





ORDERIN	IG INFORM	ATION						
	ENVIR	ONMENTAL AND QUALITY CODE			PACKAG	ING CODE		
PART NUMBER (EXAMPLE)	AEC-Q101 QUALIFIED	RoHS-CON LEAD (P		TIN PLATED	3K PER 7" REEL (8 mm TAPE),	10K PER 13" REEL (8 mm TAPE),	ORDERING CODE (EXAMPLE)	
	QUALIFIED	STANDARD	GREEN	PLATED	15K/BOX = MÔQ	15K/BOX = MOQ 10K/BOX = MO		
GSOT05-		E		3	-08		GSOT05-E3-08	
GSOT05-			G	3	-08		GSOT05-G3-08	
GSOT05-	Н	E		3	-08		GSOT05-HE3-08	
GSOT05-	Н		G	3	-08		GSOT05-HG3-08	
GSOT05-		E		3		-18	GSOT05-E3-18	
GSOT05-			G	3		-18	GSOT05-G3-18	
GSOT05-	Н	E		3		-18	GSOT05-HE3-18	
GSOT05-	Н		G	3		-18	GSOT05-HG3-18	

PACKA		1					
DEVICE NAME	PACKAGE NAME	TYPE CODE	ENVIRONMENTAL STATUS	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS
GSOT03	SOT-23	03	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
400100	001 20	03G	Green	8.1 mg	020110	(according J-STD-020)	
GSOT04	SOT-23	04	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030104	501-25	04G	Green	8.1 mg 0L 94 V-0		(according J-STD-020)	
GSOT05	SOT-23	05	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030103	301-23	05G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	200 C/10 S at terminals
GSOT08	SOT-23	08	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030108	301-23	08G	Green	8.1 mg	0L 94 V-0	(according J-STD-020)	200 C/10 S at terminals
GSOT12	SOT-23	12	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
G30112	301-23	12G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	200 C/TO'S at terminals
GSOT15	SOT-23	15	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
630115	301-23	15G	Green	8.1 mg	UL 94 V-0	(according J-STD-020)	200 C/TO'S at terminals
GSOT24	SOT-23	24	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
630124	301-23	24G	Green	8.1 mg	02 94 0-0	(according J-STD-020)	200 C/10 S at terminals
GSOT36	SOT-23	36	Standard	8.8 mg	UL 94 V-0	MSL level 1	260 °C/10 s at terminals
030130	301-23	36G	Green	8.1 mg	02 94 0-0	(according J-STD-020)	200 Or to s at terminals

Rev. 2.5, 02-May-17

1 For technical questions, contact: <u>ESDprotection@vishay.com</u> Document Number: 85807

THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



www.vishay.com

Vishay Semiconductors

ABSOLUTE MAXIMUM RATINGS GSOT03						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}	30	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	369	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD initiduity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT04						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	30	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	429	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT05							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}	30	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	480	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	± 30	kV			
ESD Infinutility	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT08						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	18	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	345	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		



ABSOLUTE MAXIMUM RATINGS GSOT12							
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT			
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	I _{PPM}	12	А			
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, $t_p = 8/20 \ \mu s$; single shot	P _{PP}	312	W			
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV			
	Air discharge acc. IEC 61000-4-2; 10 pulses	VESD	± 30	kV			
Operating temperature	Junction temperature	TJ	-40 to +125	°C			
Storage temperature		T _{STG}	-55 to +150	°C			

ABSOLUTE MAXIMUM RATINGS GSOT15						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	8	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	230	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT24						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	235	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		

ABSOLUTE MAXIMUM RATINGS GSOT36						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	I _{PPM}	3.5	А		
Peak pulse power	Pin 3 to 1 acc. IEC 61000-4-5, t _p = 8/20 μs; single shot	P _{PP}	248	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	N/	± 30	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V _{ESD}	± 30	kV		
Operating temperature	Junction temperature	TJ	-40 to +125	°C		
Storage temperature		T _{STG}	-55 to +150	°C		





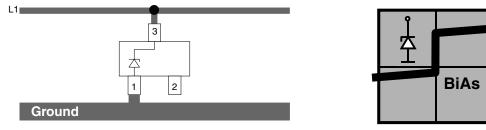
BIAs-MODE (1-line Bidirectional Asymmetrical protection mode)

With the GSOTxx one signal- or data-lines (L1) can be protected against voltage transients. With pin 1 connected to ground and pin 3 connected to a signal- or data-line which has to be protected. As long as the voltage level on the data- or signal-line is between 0 V (ground level) and the specified maximum reverse working voltage (V_{RWM}) the protection diode between pin 1 and pin 3 offers a high isolation to the ground line. The protection device behaves like an open switch.

As soon as any positive transient voltage signal exceeds the breakdown voltage level of the protection diode, the diode becomes conductive and shorts the transient current to ground. Now the protection device behaves like a closed switch. The clamping voltage (V_C) is defined by the breakdown voltage (V_{BR}) level plus the voltage drop at the series impedance (resistance and inductance) of the protection diode.

Any negative transient signal will be clamped accordingly. The negative transient current is flowing in the forward direction through the protection diode. The low forward voltage (V_F) clamps the negative transient close to the ground level.

Due to the different clamping levels in forward and reverse direction the GSOTxx clamping behavior is Bidirectional and Asymmetrical (BiAs).



²⁰⁴²²

ELECTRICAL CHARACTERISTICS GSOT03 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1							
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT	
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines	
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	3.3	V	
Reverse voltage	at I _R = 100 μA	V _R	3.3	-	-	V	
Reverse current	at V _R = 3.3 V	I _R	-	-	100	μA	
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	4	4.6	5.5	V	
	at I _{PP} = 1 A	V	-	5.7	7.5	V	
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	10	12.3	V	
Forward elemping valtage	at I _{PP} = 1 A	V	-	1	1.2	V	
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V	
Canaaitanaa	at $V_R = 0 V$; f = 1 MHz	0	-	420	600	pF	
Capacitance	at V _R = 1.6 V; f = 1 MHz	C _D	-	260	-	pF	

ELECTRICAL CHARACTERISTICS GSOT04 ($T_{amb} = 25$ °C unless otherwise specified) between pin 3 and pin 1								
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT		
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines		
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	4	V		
Reverse voltage	at I _R = 20 μA	V _R	4	-	-	V		
Reverse current	at V _R = 4 V	I _R	-	-	20	μA		
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	5	6.1	7	V		
Deverse elemeine veltage	at I _{PP} = 1 A	V	-	7.5	9	V		
Reverse clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _C	-	11.2	14.3	V		
	at I _{PP} = 1 A	N	-	1	1.2	V		
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V		
Orneritener	at $V_R = 0 V$; f = 1 MHz	0	-	310	450	pF		
Capacitance	at $V_R = 2 V$; f = 1 MHz	C _D	-	200	-	pF		

Rev. 2.5, 02-May-17

Document Number: 85807

For technical questions, contact: <u>ESDprotection@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



ELECTRICAL CHARACE between pin 3 and pin 1	CTERISTICS GSOT05 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	5	V
Reverse voltage	at I _R = 10 μA	V _R	5	-	-	V
Reverse current	at V _R = 5 V	I _R	-	-	10	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	6	6.8	8	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	7	8.7	V
	at $I_{PP} = I_{PPM} = 30 \text{ A}$		-	12	16	V
	at I _{PP} = 1 A	N	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 30 A	V _F	-	4.5	-	V
Capacitance	at $V_R = 0$ V; f = 1 MHz	C _D	-	260	350	pF
	at V _R = 2.5 V; f = 1 MHz		-	150	-	pF

ELECTRICAL CHARACTERISTICS GSOT08 (T_{amb} = 25 °C unless otherwise specified) between pin 3 and pin 1

between pin 3 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	8	V
Reverse voltage	at I _R = 5 µA	V _R	8	-	-	V
Reverse current	at V _R = 8 V	I _R	-	-	5	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	9	10	11	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	10.7	13	V
	at I _{PP} = I _{PPM} = 18 A		-	15.2	19.2	V
Forward elemping valtage	at I _{PP} = 1 A	- V _F	-	1	1.2	V
Forward clamping voltage	at I _{PP} = I _{PPM} = 18 A		-	3	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	C	-	160	250	pF
	at V _R = 4 V; f = 1 MHz	C _D	-	80	-	pF

ELECTRICAL CHARAC between pin 3 and pin 1	TERISTICS GSOT12 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	12	V
Reverse voltage	at I _R = 1 μA	V _R	12	-	-	V
Reverse current	at V _R = 12 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	13.5	15	16.5	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	15.4	18.7	V
	at I _{PP} = I _{PPM} = 12 A		-	21.2	26	V
Forward clamping voltage	at I _{PP} = 1 A	N/	-	1	1.2	V
	at I _{PP} = I _{PPM} = 12 A	V _F	-	2.2	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	CD	-	115	150	pF
	at $V_R = 6 V$; f = 1 MHz		-	50	-	pF

GSOT03 to GSOT36



Vishay Semiconductors

ELECTRICAL CHARACE between pin 3 and pin 1	TERISTICS GSOT15 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	15	V
Reverse voltage	at I _R = 1 μA	V _R	15	-	-	V
Reverse current	at V _R = 15 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	16.5	18	20	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	19.4	23.5	V
	at I _{PP} = I _{PPM} = 8 A		-	24.8	28.8	V
Forward clamping voltage	at I _{PP} = 1 A	V	-	1	1.2	V
	at I _{PP} = I _{PPM} = 8 A	V _F	-	1.8	-	V
Capacitance	at $V_R = 0$ V; f = 1 MHz	C _D	-	90	120	pF
	at V _R = 7.5 V; f = 1 MHz		-	35	-	pF

ELECTRICAL CHARACTERISTICS GSOT24 ($T_{amb} = 25 \text{ °C}$ unless otherwise specified) between pin 3 and pin 1

between pin 5 and pin 1						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	24	V
Reverse voltage	at I _R = 1 μA	V _R	24	-	-	V
Reverse current	at $V_R = 24 V$	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	27	30	33	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	34	41	V
	at $I_{PP} = I_{PPM} = 5 A$		-	41	47	V
Forward alamping valtage	at I _{PP} = 1 A		-	1	1.2	V
Forward clamping voltage	at $I_{PP} = I_{PPM} = 5 A$		-	1.4	-	V
Capacitance	at $V_R = 0 V$; f = 1 MHz	- C _D	-	65	80	pF
	at V _R = 12 V; f = 1 MHz		-	20	-	pF

ELECTRICAL CHARACE between pin 3 and pin 1	TERISTICS GSOT36 (T _{amb} = 25 °C	C unless ot	herwise s	pecified)		
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N _{channel}	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V _{RWM}	-	-	36	V
Reverse voltage	at I _R = 1 μA	V _R	36	-	-	V
Reverse current	at V _R = 36 V	I _R	-	-	1	μA
Reverse breakdown voltage	at I _R = 1 mA	V _{BR}	39	43	47	V
Reverse clamping voltage	at I _{PP} = 1 A	V _C	-	49	60	V
	at I _{PP} = I _{PPM} = 3.5 A		-	59	71	V
Forward clamping voltage	at I _{PP} = 1 A	- V _F	-	1	1.2	V
	at I _{PP} = I _{PPM} = 3.5 A		-	1.3	-	V
Capacitance	at $V_R = 0$ V; f = 1 MHz	CD	-	52	65	pF
	at $V_B = 18$ V; f = 1 MHz		-	12	-	pF



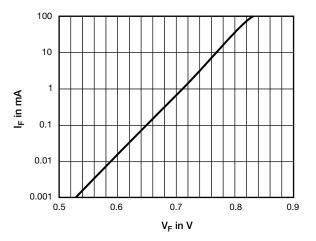


Fig. 1 - Typical Forward Current I_F vs. Forward Voltage V_F

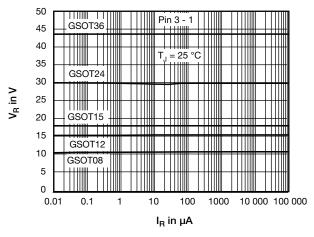


Fig. 2 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

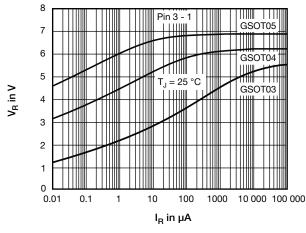


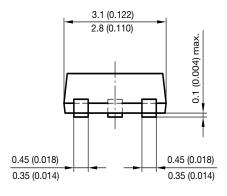
Fig. 3 - Typical Reverse Voltage V_{R} vs. Reverse Current I_{R}

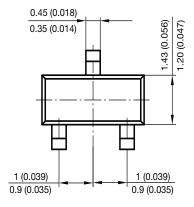
Rev. 2.5, 02-May-17

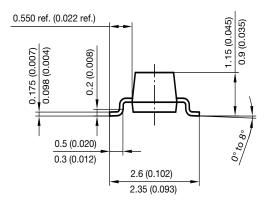
7



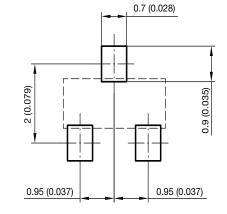
PACKAGE DIMENSIONS in millimeters (inches): SOT-23



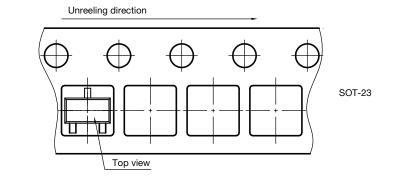




Foot print recommendation:



Document no.: 6.541-5014.01-4 Rev. 8 - Date: 23.Sept.2009 17418



Orientation in carrier tape SOT-23 S8-V-3929.01-006 (4) 04.02.2010 22607

8



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.